

Refine Search

10/630,969

Search Results -

| Terms | Documents |
|--|-----------|
| L5 and (hfo2 or zro2 or ta2o5 or tio2 or aL2o3 or hfsio) | 1 |

Database:

US Pre-Grant Publication Full-Text Database
 US Patents Full-Text Database
 US OCR Full-Text Database
 EPO Abstracts Database
 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search:

L6

Refine Search

Recall Text

Clear

Interrupt

Search History

 DATE: Tuesday, June 29, 2004 [Printable Copy](#) [Create Case](#)

| <u>Set Name</u> | <u>Query</u> | <u>Hit Count</u> | <u>Set Name</u> result set |
|---------------------------|--|------------------|-------------------------------|
| side by side | | | |
| DB=USPT; PLUR=YES; OP=ADJ | | | |
| <u>L6</u> | L5 and (hfo2 or zro2 or ta2o5 or tio2 or aL2o3 or hfsio) | 1 | <u>L6</u> |
| <u>L5</u> | L3 and oxidation | 20 | <u>L5</u> |
| <u>L4</u> | L3 and oxidation and (sio2) | 0 | <u>L4</u> |
| <u>L3</u> | L2 and (inert or argon or ar or heliumn or he or neon or ne or kr or krypton or xenon or nitrogen) | 45 | <u>L3</u> |
| <u>L2</u> | L1 and ((ratio) near3 (nitrogen and oxygen)) | 45 | <u>L2</u> |
| <u>L1</u> | microstructure | 23090 | <u>L1</u> |

END OF SEARCH HISTORY

Hit List

| | | | | |
|---------------|---------------------|-------|----------|-----------|
| Clear | Generate Collection | Print | Fwd Refs | Bkwd Refs |
| Generate OACS | | | | |

Search Results - Record(s) 1 through 1 of 1 returned.

☐ 1. Document ID: US 6071601 A

L6: Entry 1 of 1

File: USPT

Jun 6, 2000

US-PAT-NO: 6071601

DOCUMENT-IDENTIFIER: US 6071601 A

TITLE: Coated cutting tool member

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | RWC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|

| | | | | | |
|-------|---------------------|-------|----------|-----------|---------------|
| Clear | Generate Collection | Print | Fwd Refs | Bkwd Refs | Generate OACS |
|-------|---------------------|-------|----------|-----------|---------------|

| Terms | Documents |
|--|-----------|
| L5 and (hfo2 or zro2 or ta2o5 or tio2 or aL2o3 or hfsio) | 1 |

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Refine Search

Search Results -

| Terms | Documents |
|--------------------------|-----------|
| L5 and pressure and torr | 5 |

Database:

US Pre-Grant Publication Full-Text Database
 US Patents Full-Text Database
 US OCR Full-Text Database
 EPO Abstracts Database
 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search:

L7

Search History

 DATE: Tuesday, June 29, 2004 [Printable Copy](#) [Create Case](#)

| <u>Set Name</u> side by side | <u>Query</u> | <u>Hit Count</u> | <u>Set Name</u> result set |
|----------------------------------|--|------------------|-------------------------------|
| <i>DB=USPT; PLUR=YES; OP=ADJ</i> | | | |
| <u>L7</u> | L5 and pressure and torr | 5 | <u>L7</u> |
| <u>L6</u> | L5 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio) | 1 | <u>L6</u> |
| <u>L5</u> | L3 and oxidation | 20 | <u>L5</u> |
| <u>L4</u> | L3 and oxidation and (sio2) | 0 | <u>L4</u> |
| <u>L3</u> | L2 and (inert or argon or ar or heliumn or he or neon or ne or kr or krypton or xenon or nitrogen) | 45 | <u>L3</u> |
| <u>L2</u> | L1 and ((ratio) near3 (nitrogen and oxygen)) | 45 | <u>L2</u> |
| <u>L1</u> | microstructure | 23090 | <u>L1</u> |

END OF SEARCH HISTORY

Hit List

[Clear](#)[Generate Collection](#)[Print](#)[Fwd Refs](#)[Bkwd Refs](#)[Generate OACS](#)

Search Results - Record(s) 1 through 5 of 5 returned.

☐ 1. Document ID: US 6498097 B1

L7: Entry 1 of 5

File: USPT

Dec 24, 2002

US-PAT-NO: 6498097

DOCUMENT-IDENTIFIER: US 6498097 B1

TITLE: Apparatus and method of forming preferred orientation-controlled platinum film using oxygen

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KMC | Draw. De |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|----------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|----------|

☐ 2. Document ID: US 6071601 A

L7: Entry 2 of 5

File: USPT

Jun 6, 2000

US-PAT-NO: 6071601

DOCUMENT-IDENTIFIER: US 6071601 A

TITLE: Coated cutting tool member

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KMC | Draw. De |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|----------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|----------|

☐ 3. Document ID: US 6054331 A

L7: Entry 3 of 5

File: USPT

Apr 25, 2000

US-PAT-NO: 6054331

DOCUMENT-IDENTIFIER: US 6054331 A

TITLE: Apparatus and methods of depositing a platinum film with anti-oxidizing function over a substrate

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KMC | Draw. De |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|----------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|----------|

☐ 4. Document ID: US 5143879 A

L7: Entry 4 of 5

File: USPT

Sep 1, 1992

US-PAT-NO: 5143879

DOCUMENT-IDENTIFIER: US 5143879 A

**** See image for Certificate of Correction ****

TITLE: Method to recover organic templates from freshly synthesized molecular sieves

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KMC | Draw. Doc |
|------|-------|----------|-------|--------|----------------|------|-----------|--------|-----|-----------|
|------|-------|----------|-------|--------|----------------|------|-----------|--------|-----|-----------|

☐ 5. Document ID: US 4762728 A

L7: Entry 5 of 5

File: USPT

Aug 9, 1988

US-PAT-NO: 4762728

DOCUMENT-IDENTIFIER: US 4762728 A

TITLE: Low temperature plasma nitridation process and applications of nitride films formed thereby

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KMC | Draw. Doc |
|------|-------|----------|-------|--------|----------------|------|-----------|--------|-----|-----------|
|------|-------|----------|-------|--------|----------------|------|-----------|--------|-----|-----------|

Terms

Documents

L5 and pressure and torr

5

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Hit List

10/630,969

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|---------------|---------------------|-------|----------|-----------|
| Clear | Generate Collection | Print | Fwd Refs | Bkwd Refs |
| Generate OACS | | | | |

Search Results - Record(s) 1 through 4 of 4 returned.

☐ 1. Document ID: US 6548343 B1

L24: Entry 1 of 4

File: USPT

Apr 15, 2003

US-PAT-NO: 6548343

DOCUMENT-IDENTIFIER: US 6548343 B1

TITLE: Method of fabricating a ferroelectric memory cell

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KMC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|

☐ 2. Document ID: US 6485988 B2

L24: Entry 2 of 4

File: USPT

Nov 26, 2002

US-PAT-NO: 6485988

DOCUMENT-IDENTIFIER: US 6485988 B2

TITLE: Hydrogen-free contact etch for ferroelectric capacitor formation

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KMC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|

☐ 3. Document ID: US 6413386 B1

L24: Entry 3 of 4

File: USPT

Jul 2, 2002

US-PAT-NO: 6413386

DOCUMENT-IDENTIFIER: US 6413386 B1

TITLE: Reactive sputtering method for forming metal-silicon layer

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KMC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|

☐ 4. Document ID: US 6362093 B1

L24: Entry 4 of 4

File: USPT

Mar 26, 2002

US-PAT-NO: 6362093

DOCUMENT-IDENTIFIER: US 6362093 B1

TITLE: Dual damascene method employing sacrificial via fill layer

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWIC | Draw. Des |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|-----------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|-----------|

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| Clear | Generate Collection | Print | Fwd Refs | Bkwd Refs | Generate OACS |
|-------|---------------------|-------|----------|-----------|---------------|

| | |
|----------------------------------|-----------|
| Terms | Documents |
| L23 and (silicon adj oxynitride) | 4 |

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Refine Search

Search Results -

| Terms | Documents |
|----------------------------------|-----------|
| L23 and (silicon adj oxynitride) | 4 |

Database:

US Pre-Grant Publication Full-Text Database
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 EPO Abstracts Database
 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search:

L24

Refine Search

Recall Text



Clear

Interrupt

Search History

 DATE: Tuesday, June 29, 2004 [Printable Copy](#) [Create Case](#)

| <u>Set Name</u> | <u>Query</u> | <u>Hit Count</u> | <u>Set Name</u> result set |
|----------------------------------|---|------------------|-------------------------------|
| <i>DB=USPT; PLUR=YES; OP=ADJ</i> | | | |
| <u>L24</u> | L23 and (silicon adj oxynitride) | 4 | <u>L24</u> |
| <u>L23</u> | L22 and (silicon adj oxide) | 7 | <u>L23</u> |
| <u>L22</u> | L21 and oxide and (oxygen adj containing) | 11 | <u>L22</u> |
| <u>L21</u> | L20 and semiconductor and (flow adj rate) | 80 | <u>L21</u> |
| <u>L20</u> | L19 and (inert or h2 or ne or ar or xe or neon or argon or krypton or kr) | 1159 | <u>L20</u> |
| <u>L19</u> | (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio) | 2645 | <u>L19</u> |
| <u>L18</u> | L2 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio) | 0 | <u>L18</u> |
| <u>L17</u> | L11 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio) | 0 | <u>L17</u> |
| <u>L16</u> | L15 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio) | 0 | <u>L16</u> |
| <u>L15</u> | L11 and (inert or argon or neon or hydrogen or xenon or krypton) | 56 | <u>L15</u> |
| <u>L14</u> | L11 and (inert or argon or neon or hydrogen or xenon or krypton) and (high adj K) | 0 | <u>L14</u> |
| <u>L13</u> | L11 near10 ((nitrogen and oxygen) or (n2 and o2)) | 0 | <u>L13</u> |

| | | | |
|------------|---|-----|------------|
| <u>L12</u> | L11 near5 ((nitrogen and oxygen) or (n2 and o2)) | 0 | <u>L12</u> |
| <u>L11</u> | (flow adj rate) near4 (3:1) | 76 | <u>L11</u> |
| <u>L10</u> | l2 and (3:1) | 8 | <u>L10</u> |
| <u>L9</u> | l2 and (nitrogen:oxygen) | 0 | <u>L9</u> |
| <u>L8</u> | n2:o2 | 2 | <u>L8</u> |
| <u>L7</u> | L4 and (high adj K) and oxidation and chamber | 3 | <u>L7</u> |
| <u>L6</u> | L5 and (silicon adj oxide) | 9 | <u>L6</u> |
| <u>L5</u> | L4 and (oxygen adj containing) | 19 | <u>L5</u> |
| <u>L4</u> | L2 and nitrogen and oxygen and (inert or hydrogen or argon or h2 or ar or xenon or xe or krypton or kr or neon or ne) | 88 | <u>L4</u> |
| <u>L3</u> | L2 and ((nitrogen and oxygen) near2 (ratio)) | 3 | <u>L3</u> |
| <u>L2</u> | (semiconductor or wafer) and (micro) and (flow near ratio) | 231 | <u>L2</u> |
| <u>L1</u> | microstructure near5 (flow ratio) | 2 | <u>L1</u> |

END OF SEARCH HISTORY

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| Clear | Generate Collection | Print | Fwd Refs | Bkwd Refs |
| Generate OACS | | | | |

Search Results - Record(s) 1 through 7 of 7 returned.

☐ 1. Document ID: US 6620670 B2

L23: Entry 1 of 7

File: USPT

Sep 16, 2003

US-PAT-NO: 6620670

DOCUMENT-IDENTIFIER: US 6620670 B2

TITLE: Process conditions and precursors for atomic layer deposition (ALD) of AL2O3

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWIC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|--------|

☐ 2. Document ID: US 6583463 B1

L23: Entry 2 of 7

File: USPT

Jun 24, 2003

US-PAT-NO: 6583463

DOCUMENT-IDENTIFIER: US 6583463 B1

TITLE: Semiconductor integrated circuit device with information storage capacitor having ruthenium dioxide lower electrode and crystallized TA2O5 capacitor insulator

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWIC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|--------|

☐ 3. Document ID: US 6548343 B1

L23: Entry 3 of 7

File: USPT

Apr 15, 2003

US-PAT-NO: 6548343

DOCUMENT-IDENTIFIER: US 6548343 B1

TITLE: Method of fabricating a ferroelectric memory cell

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWIC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|--------|

☐ 4. Document ID: US 6544875 B1

L23: Entry 4 of 7

File: USPT

Apr 8, 2003

US-PAT-NO: 6544875

DOCUMENT-IDENTIFIER: US 6544875 B1

TITLE: Chemical vapor deposition of silicate high dielectric constant materials

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWC | Draw De |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|---------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|---------|

☐ 5. Document ID: US 6485988 B2

L23: Entry 5 of 7

File: USPT

Nov 26, 2002

US-PAT-NO: 6485988

DOCUMENT-IDENTIFIER: US 6485988 B2

TITLE: Hydrogen-free contact etch for ferroelectric capacitor formation

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWC | Draw De |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|---------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|---------|

☐ 6. Document ID: US 6413386 B1

L23: Entry 6 of 7

File: USPT

Jul 2, 2002

US-PAT-NO: 6413386

DOCUMENT-IDENTIFIER: US 6413386 B1

TITLE: Reactive sputtering method for forming metal-silicon layer

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWC | Draw De |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|---------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|---------|

☐ 7. Document ID: US 6362093 B1

L23: Entry 7 of 7

File: USPT

Mar 26, 2002

US-PAT-NO: 6362093

DOCUMENT-IDENTIFIER: US 6362093 B1

TITLE: Dual damascene method employing sacrificial via fill layer

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWC | Draw De |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|---------|
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Fwd Refs

Bkwd Refs

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Terms

Documents

L22 and (silicon adj oxide)

7

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| Clear | Generate Collection | Print | Fwd Refs | Bkwd Refs |
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Search Results - Record(s) 1 through 10 of 11 returned.

☐ 1. Document ID: US 6659111 B1

L22: Entry 1 of 11

File: USPT

Dec 9, 2003

US-PAT-NO: 6659111

DOCUMENT-IDENTIFIER: US 6659111 B1

TITLE: Cleaning gas and method for cleaning vacuum treatment apparatus by flowing the cleaning gas

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KMC | Draw De |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|---------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|---------|

☐ 2. Document ID: US 6620670 B2

L22: Entry 2 of 11

File: USPT

Sep 16, 2003

US-PAT-NO: 6620670

DOCUMENT-IDENTIFIER: US 6620670 B2

TITLE: Process conditions and precursors for atomic layer deposition (ALD) of AL2O3

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KMC | Draw De |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|---------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|---------|

☐ 3. Document ID: US 6583463 B1

L22: Entry 3 of 11

File: USPT

Jun 24, 2003

US-PAT-NO: 6583463

DOCUMENT-IDENTIFIER: US 6583463 B1

TITLE: Semiconductor integrated circuit device with information storage capacitor having ruthenium dioxide lower electrode and crystallized TA2O5 capacitor insulator

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KMC | Draw De |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|---------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|---------|

☐ 4. Document ID: US 6548343 B1

L22: Entry 4 of 11

File: USPT

Apr 15, 2003

US-PAT-NO: 6548343

DOCUMENT-IDENTIFIER: US 6548343 B1

TITLE: Method of fabricating a ferroelectric memory cell

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWIC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|--------|

☐ 5. Document ID: US 6544875 B1

L22: Entry 5 of 11

File: USPT

Apr 8, 2003

US-PAT-NO: 6544875

DOCUMENT-IDENTIFIER: US 6544875 B1

TITLE: Chemical vapor deposition of silicate high dielectric constant materials

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWIC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|--------|

☐ 6. Document ID: US 6509511 B1

L22: Entry 6 of 11

File: USPT

Jan 21, 2003

US-PAT-NO: 6509511

DOCUMENT-IDENTIFIER: US 6509511 B1

TITLE: Process for the conversion of perfluoroalkanes, a catalyst for use therein and a method for its preparation

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWIC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|--------|

☐ 7. Document ID: US 6485988 B2

L22: Entry 7 of 11

File: USPT

Nov 26, 2002

US-PAT-NO: 6485988

DOCUMENT-IDENTIFIER: US 6485988 B2

TITLE: Hydrogen-free contact etch for ferroelectric capacitor formation

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWIC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|--------|

☐ 8. Document ID: US 6413386 B1

L22: Entry 8 of 11

File: USPT

Jul 2, 2002

US-PAT-NO: 6413386

DOCUMENT-IDENTIFIER: US 6413386 B1

TITLE: Reactive sputtering method for forming metal-silicon layer

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KMC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|

☐ 9. Document ID: US 6362093 B1

L22: Entry 9 of 11

File: USPT

Mar 26, 2002

US-PAT-NO: 6362093

DOCUMENT-IDENTIFIER: US 6362093 B1

TITLE: Dual damascene method employing sacrificial via fill layer

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KMC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|

☐ 10. Document ID: US 6238582 B1

L22: Entry 10 of 11

File: USPT

May 29, 2001

US-PAT-NO: 6238582

DOCUMENT-IDENTIFIER: US 6238582 B1

TITLE: Reactive ion beam etching method and a thin film head fabricated using the method

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KMC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|

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| Clear | Generate Collection | Print | Fwd Refs | Bkwd Refs | Generate OACS |
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| | |
|---|-----------|
| Terms | Documents |
| L21 and oxide and (oxygen adj containing) | 11 |

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| Clear | Generate Collection | Print | Fwd Refs | Bkwd Refs |
| Generate OACS | | | | |

Search Results - Record(s) 11 through 11 of 11 returned.

☐ 11. Document ID: US 6218300 B1

L22: Entry 11 of 11

File: USPT

Apr 17, 2001

US-PAT-NO: 6218300

DOCUMENT-IDENTIFIER: US 6218300 B1

TITLE: Method and apparatus for forming a titanium doped tantalum pentaoxide dielectric layer using CVD

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KMC | Draw D |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|-----|--------|

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| Clear | Generate Collection | Print | Fwd Refs | Bkwd Refs | Generate OACS |
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| | |
|---|-----------|
| Terms | Documents |
| L21 and oxide and (oxygen adj containing) | 11 |

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Search Results - Record(s) 1 through 3 of 3 returned.

☐ 1. Document ID: US 6387819 B1

L3: Entry 1 of 3

File: USPT

May 14, 2002

US-PAT-NO: 6387819

DOCUMENT-IDENTIFIER: US 6387819 B1

TITLE: Method for etching low K dielectric layers

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWIC | Draw Dc |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|---------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|---------|

☐ 2. Document ID: US 6110609 A

L3: Entry 2 of 3

File: USPT

Aug 29, 2000

US-PAT-NO: 6110609

DOCUMENT-IDENTIFIER: US 6110609 A

TITLE: Magnetic thin film and magnetic head using the same

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWIC | Draw Dc |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|---------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|---------|

☐ 3. Document ID: US 4543707 A

L3: Entry 3 of 3

File: USPT

Oct 1, 1985

US-PAT-NO: 4543707

DOCUMENT-IDENTIFIER: US 4543707 A

TITLE: Method of forming through holes by differential etching of stacked silicon oxynitride layers

| Full | Title | Citation | Front | Review | Classification | Date | Reference | | | Claims | KWIC | Draw Dc |
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|---------|
|------|-------|----------|-------|--------|----------------|------|-----------|--|--|--------|------|---------|

| Terms | Documents |
|--|-----------|
| L2 and ((nitrogen and oxygen) near2 (ratio)) | 3 |

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